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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-fl.com/product-detail/nxp-semiconductors/kmpc8358evragdga

- Data bus widths:
 - Single 32-bit data PCI interface that operates at up to 66 MHz
- PCI 3.3-V compatible (not 5-V compatible)
- PCI host bridge capabilities on both interfaces
- PCI agent mode supported on PCI interface
- Support for PCI-to-memory and memory-to-PCI streaming
- Memory prefetching of PCI read accesses and support for delayed read transactions
- Support for posting of processor-to-PCI and PCI-to-memory writes
- On-chip arbitration, supporting five masters on PCI
- Support for accesses to all PCI address spaces
- Parity support
- Selectable hardware-enforced coherency
- Address translation units for address mapping between host and peripheral
- Dual address cycle supported when the device is the target
- Internal configuration registers accessible from PCI
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)
 - Dedicated single data rate SDRAM controller
 - Parity support
 - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for 8 external and 35 internal discrete interrupt sources
 - Support for one external (optional) and seven internal machine checkstop interrupt sources
 - Programmable highest priority request
 - Four groups of interrupts with programmable priority
 - External and internal interrupts directed to communication processor
 - Redirects interrupts to external $\overline{\text{INTA}}$ pin when in core disable mode
 - Unique vector number for each interrupt source
- Dual industry-standard I²C interfaces
 - Two-wire interface

- Multiple master support
- Master or slave I²C mode support
- On-chip digital filtering rejects spikes on the bus
- System initialization data is optionally loaded from I²C-1 EPROM by boot sequencer embedded hardware
- DMA controller
 - Four independent virtual channels
 - Concurrent execution across multiple channels with programmable bandwidth control
 - All channels accessible by local core and remote PCI masters
 - Misaligned transfer capability
 - Data chaining and direct mode
 - Interrupt on completed segment and chain
 - DMA external handshake signals: $\overline{\text{DMA_DREQ}}[0:3]/\overline{\text{DMA_DACK}}[0:3]/\overline{\text{DMA_DONE}}[0:3]$. There is one set for each DMA channel. The pins are multiplexed to the parallel IO pins with other QE functions.
- DUART
 - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
 - Programming model compatible with the original 16450 UART and the PC16550D
- System timers
 - Periodic interrupt timer
 - Real-time clock
 - Software watchdog timer
 - Eight general-purpose timers
- IEEE Std. 1149.1™-compliant, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8358E. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	$OV_{DD} = 3.3\text{ V}$
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode) ¹	$GV_{DD} = 2.5\text{ V}$
DDR2 signal	18 36 (half-strength mode) ¹	$GV_{DD} = 1.8\text{ V}$
10/100/1000 Ethernet signals	42	$LV_{DD} = 2.5/3.3\text{ V}$
DUART, system control, I ² C, SPI, JTAG	42	$OV_{DD} = 3.3\text{ V}$
GPIO signals	42	$OV_{DD} = 3.3\text{ V}$ $LV_{DD} = 2.5/3.3\text{ V}$

¹ DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8358E.

2.2.1 Power-Up Sequencing

MPC8358E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD} , LV_{DD} , and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} , LV_{DD} , and OV_{DD}) and assert $\overline{PORESET}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the device.

Table 6. CLKIN DC Electrical Characteristics

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	$OV_{DD} + 0.3$	V
Input low voltage	—	V_{IL}	−0.3	0.4	V
CLKIN input current	$0\text{ V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0\text{ V} \leq V_{IN} \leq 0.5\text{ V}$ or $OV_{DD} - 0.5\text{ V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0.5\text{ V} \leq V_{IN} \leq OV_{DD} - 0.5\text{ V}$	I_{IN}	—	±100	μA

4.2 AC Electrical Characteristics

The primary clock source for the device can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

- Caution:** The system, core, USB, security, and 10/100/1000 Ethernet must not exceed their respective maximum or minimum operating frequencies.
- Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 V and 2.7 V.
- Timing is guaranteed by design and characterization.
- This represents the total input jitter—short term and long term—and is guaranteed by design.
- The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at −20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

4.3 Gigabit Reference Clock Input Timing

Table 8 provides the Gigabit reference clocks (GTX_CLK125) AC timing specifications.

Table 8. GTX_CLK125 AC Timing Specifications

At recommended operating conditions with $V_{DD} = 2.5 \pm 0.125$ mV/ 3.3 ± 0.165 mV

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
GTX_CLK125 frequency	t_{G125}	—	125	—	MHz	—
GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
GTX_CLK rise and fall time $V_{DD} = 2.5$ V $V_{DD} = 3.3$ V	t_{G125R}/t_{G125F}	—	—	0.75 1.0	ns	1
GTX_CLK125 duty cycle GMII & TBI 1000Base-T for RGMII & RTBI	t_{G125H}/t_{G125L}	45 47	—	55 53	%	2
GTX_CLK125 jitter	—	—	—	± 150	ps	2

Notes:

1. Rise and fall times for GTX_CLK125 are measured from 0.5 and 2.0 V for $V_{DD} = 2.5$ V and from 0.6 and 2.7 V for $V_{DD} = 3.3$ V.
2. GTX_CLK125 is used to generate the GTX clock for the UCC Ethernet transmitter with 2% degradation. The GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by GTX_CLK. See Section 8.2.2, "MII AC Timing Specifications," Section 8.2.3, "RMII AC Timing Specifications," and Section 8.2.5, "RGMII and RTBI AC Timing Specifications" for the duty cycle for 10Base-T and 100Base-T reference clock.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8358E.

5.1 RESET DC Electrical Characteristics

Table 9 provides the DC electrical characteristics for the RESET pins of the device.

Table 9. RESET Pins DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	−0.3	0.8	V
Input current	I_{IN}	—	—	± 10	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0$ mA	—	0.5	V

Table 12. QUICC Engine Block Operating Frequency Limitations (continued)

Interface	Interface Operating Frequency (MHz)	Max Interface Bit Rate (Mbps)	Min QUICC Engine Operating Frequency ¹ (MHz)	Notes
UART/async HDLC	3.68 (max internal ref clock)	115 (Kbps)	20	—
BISYNC	2 (max)	2	20	—
USB	48 (ref clock)	12	96	—

Notes:

1. The QUICC Engine module needs to run at a frequency higher than or equal to what is listed in this table.
2. 'F' is the actual interface operating frequency.
3. The bit rate limit is independent of the data bus width (that is, the same for serial, nibble, or octal interfaces).
4. TDM in high-speed mode for serial data interface.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR and DDR2 SDRAM interface of the MPC8358E.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

Table 13 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 13. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	—	± 10	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—
Output low current ($V_{OUT} = 0.280 \text{ V}$)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	± 10	μA	—

8.1 Three-Speed Ethernet Controller (10/100/1000 Mbps)—GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all GMII (gigabit media independent interface), MII (media independent interface), RMII (reduced media independent interface), TBI (ten-bit interface), RGMII (reduced gigabit media independent interface), and RTBI (reduced ten-bit interface) signals except MDIO (management data input/output) and MDC (management data clock). The MII, RMII, GMII, and TBI interfaces are only defined for 3.3 V, while the RGMII and RTBI interfaces are only defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet Physical Layer Device Specification Version 1.2a (9/22/2000). The electrical characteristics for the MDIO and MDC are specified in [Section 8.3, “Ethernet Management Interface Electrical Characteristics.”](#)

8.1.1 10/100/1000 Ethernet DC Electrical Characteristics

The electrical characteristics specified here apply to media independent interface (MII), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), reduced media independent interface (RMII) signals, management data input/output (MDIO) and management data clock (MDC).

The MII and RMII interfaces are defined for 3.3 V, while the RGMII and RTBI interfaces can be operated at 2.5 V. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3*. The RMII interface follows the *RMII Consortium RMII Specification Version 1.2*.

Table 24. RGMII/RTBI, GMII, TBI, MII, and RMII DC Electrical Characteristics (when operating at 3.3 V)

Parameter	Symbol	Conditions		Min	Max	Unit	Notes
Supply voltage 3.3 V	V_{DD}	—		2.97	3.63	V	1
Output high voltage	V_{OH}	$I_{OH} = -4.0 \text{ mA}$	$V_{DD} = \text{Min}$	2.40	$V_{DD} + 0.3$	V	—
Output low voltage	V_{OL}	$I_{OL} = 4.0 \text{ mA}$	$V_{DD} = \text{Min}$	GND	0.50	V	—
Input high voltage	V_{IH}	—	—	2.0	$V_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	—	—	-0.3	0.90	V	—
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq V_{DD}$		—	± 10	μA	—

Note:

1. GMII/MII pins that are not needed for RGMII, RMII, or RTBI operation are powered by the OV_{DD} supply.

Figure 13 shows the MII receive AC timing diagram.

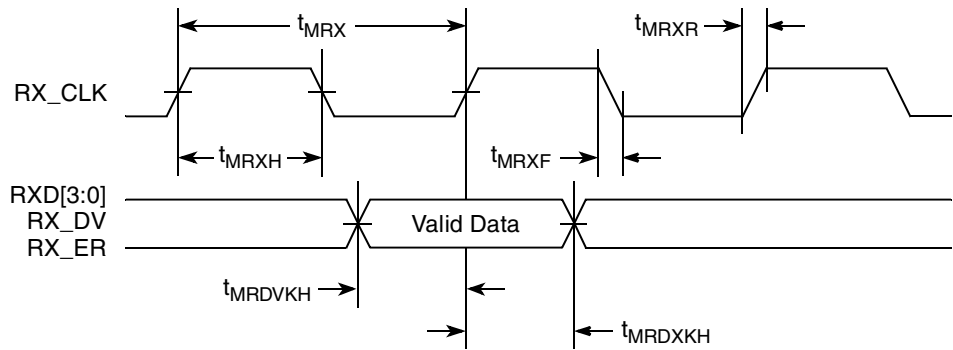


Figure 13. MII Receive AC Timing Diagram

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

Table 30 provides the RMII transmit AC timing specifications.

Table 30. RMII Transmit AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDX}$	2 —	—	— 10	ns
REF_CLK data clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(first\ three\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 17 shows the TBI transmit AC timing diagram.

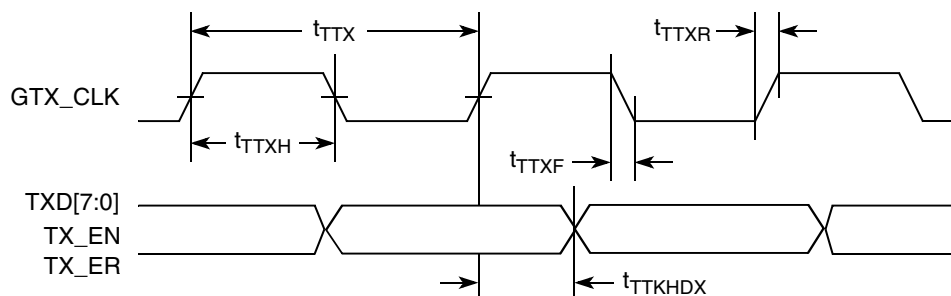


Figure 17. TBI Transmit AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

Table 33 provides the TBI receive AC timing specifications.

Table 33. TBI Receive AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
PMA_RX_CLK clock period	t_{TRX}	—	16.0	—	ns	—
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns	—
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%	—
RCG[9:0] setup time to rising PMA_RX_CLK	t_{TRDVKH}	2.5	—	—	ns	2
RCG[9:0] hold time to rising PMA_RX_CLK	t_{TRDXKH}	1.0	—	—	ns	2
RX_CLK clock rise time, $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{TRXR}	0.7	—	2.4	ns	—
RX_CLK clock fall time, $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{TRXF}	0.7	—	2.4	ns	—

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
- Setup and hold time of even numbered RCG are measured from rising edge of PMA_RX_CLK1. Setup and hold time of odd numbered RCG are measured from rising edge of PMA_RX_CLK0.

Table 36. MII Management AC Timing Specifications (continued)

At recommended operating conditions with V_{DD} is 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—	—	10	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, $t_{MDRDVKH}$ symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the ce_clk speed (that is, for a ce_clk of 200 MHz, the delay is 90 ns and for a ce_clk of 300 MHz, the delay is 63 ns).

Figure 20 shows the MII management AC timing diagram.

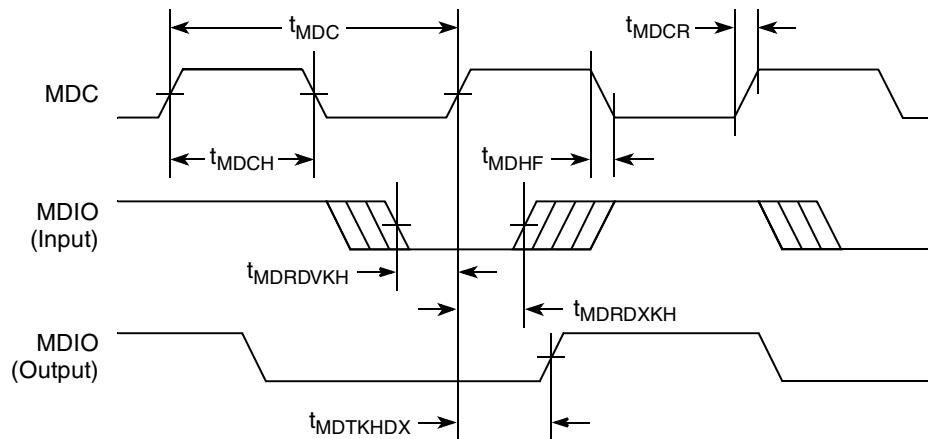


Figure 20. MII Management Interface Timing Diagram

8.3.3 IEEE 1588 Timer AC Specifications

Table 37 provides the IEEE 1588 timer AC specifications.

Table 37. IEEE 1588 Timer AC Specifications

Parameter	Symbol	Min	Max	Unit	Notes
Timer clock frequency	t_{TMRCK}	0	70	MHz	1
Input setup to timer clock	t_{TMRCKS}	—	—	—	2, 3
Input hold from timer clock	t_{TMRCKH}	—	—	—	2, 3
Output clock to output valid	t_{GCLKNV}	0	6	ns	—

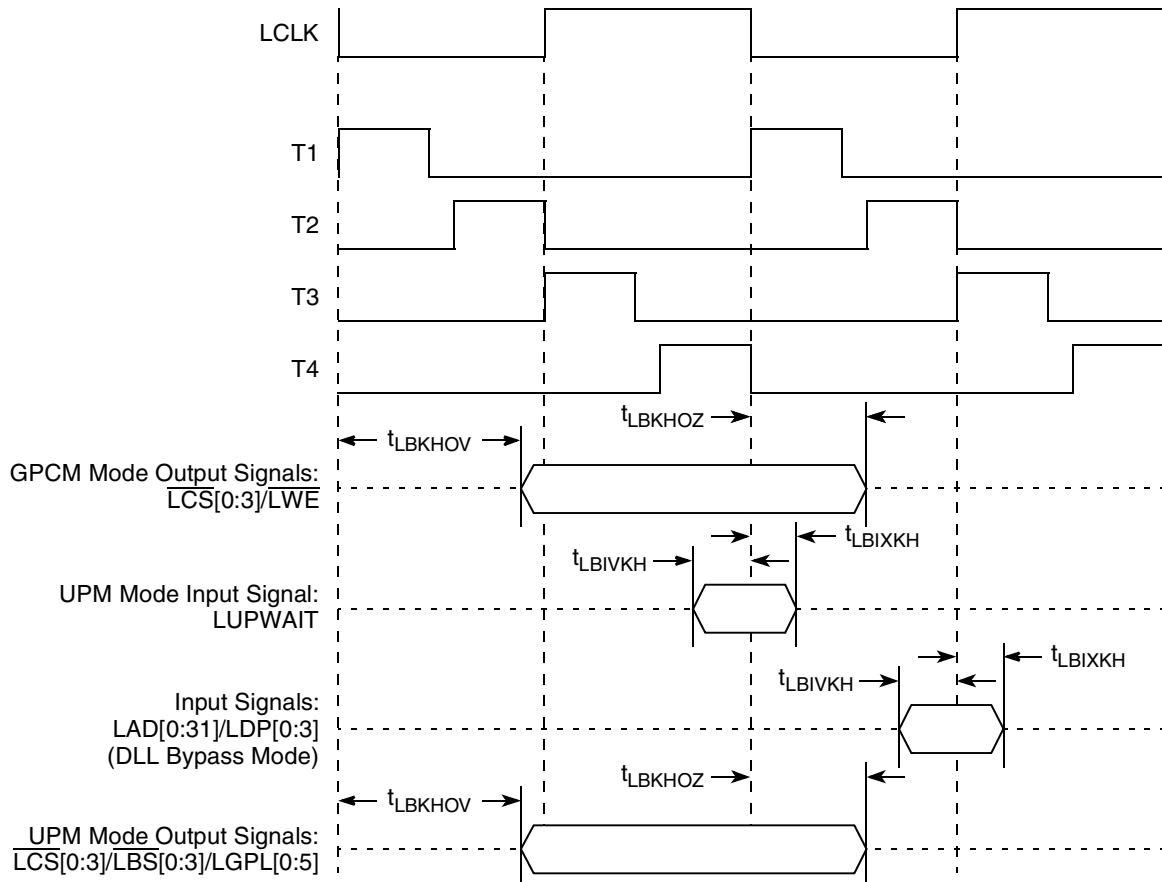


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Bypass Mode)

Figure 28 provides the AC test load for TDO and the boundary-scan outputs of the device.

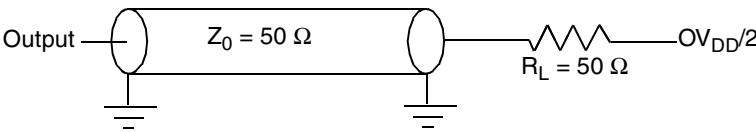


Figure 28. AC Test Load for the JTAG Interface

Figure 29 provides the JTAG clock input timing diagram.

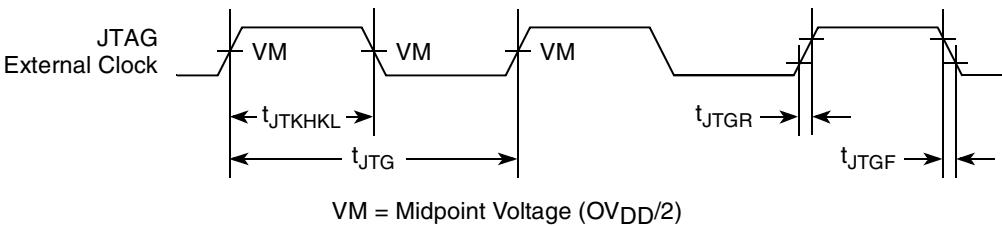


Figure 29. JTAG Clock Input Timing Diagram

Figure 30 provides the $\overline{\text{TRST}}$ timing diagram.

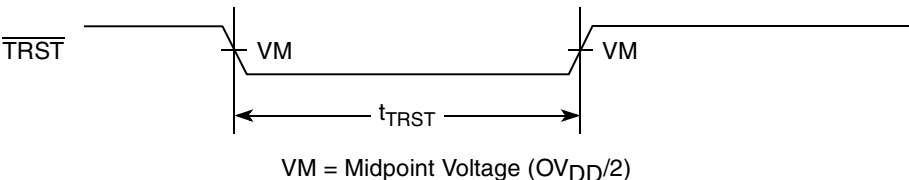


Figure 30. $\overline{\text{TRST}}$ Timing Diagram

Figure 31 provides the boundary-scan timing diagram.

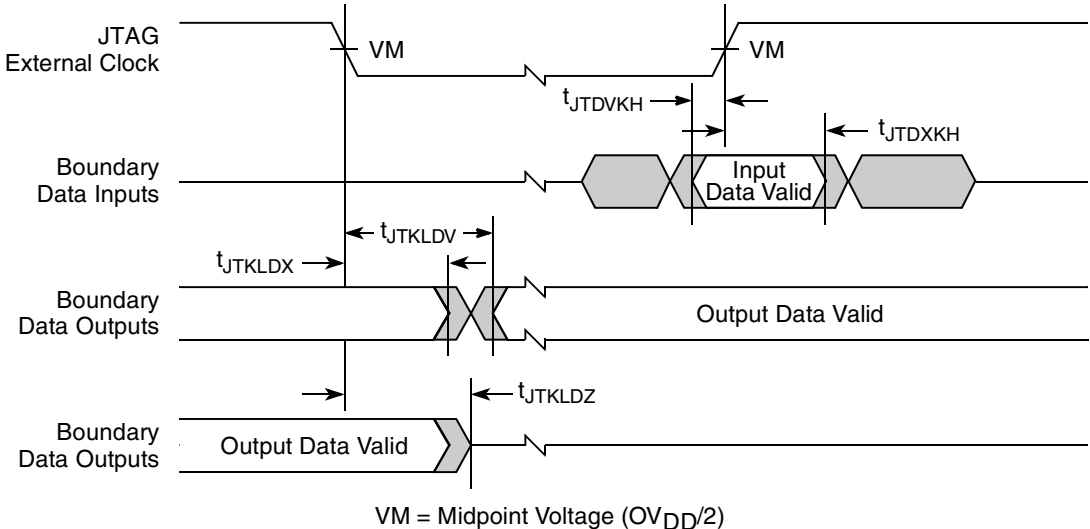


Figure 31. Boundary-Scan Timing Diagram

Table 47. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol ¹	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	7.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0.3	—	ns	2, 4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS} , reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

Figure 35 provides the AC test load for PCI.

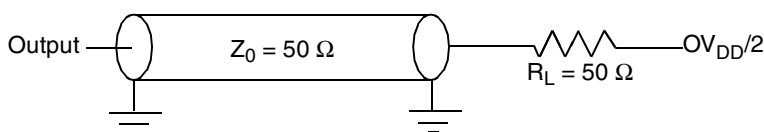

Figure 35. PCI AC Test Load

Figure 36 shows the PCI input AC timing conditions.

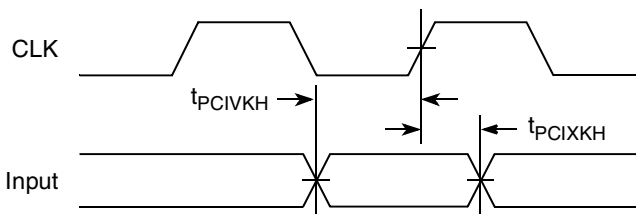
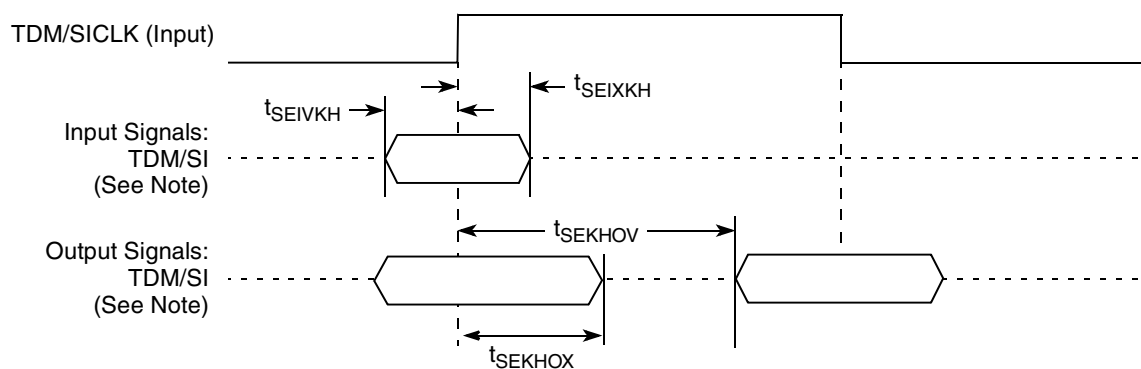

Figure 36. PCI Input AC Timing Measurement Conditions

Figure 44 shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 44. TDM/SI AC Timing (External Clock) Diagram

18 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8358E.

18.1 UTOPIA/POS DC Electrical Characteristics

Table 58 provides the DC electrical characteristics for the device UTOPIA.

Table 58. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 10	μA

18.2 UTOPIA/POS AC Timing Specifications

Table 59 provides the UTOPIA input and output AC timing specifications.

Table 59. UTOPIA AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—

Table 59. UTOPIA AC Timing Specifications¹ (continued)

Characteristic	Symbol ²	Min	Max	Unit	Notes
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4.2	—	ns	—
UTOPIA inputs—Internal clock input hold time	t_{UIIXKH}	2.4	—	ns	—
UTOPIA inputs—External clock input hold time	t_{UEIXKH}	1	—	ns	—

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{UIKHGX} symbolizes the UTOPIA outputs internal timing (UI) for the time t_{UTOPIA} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 45 provides the AC test load for the UTOPIA.

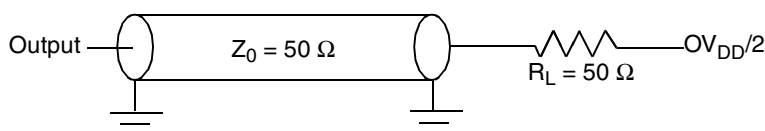

Figure 45. UTOPIA AC Test Load

Figure 46 and Figure 47 represent the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 46 shows the UTOPIA timing with external clock.

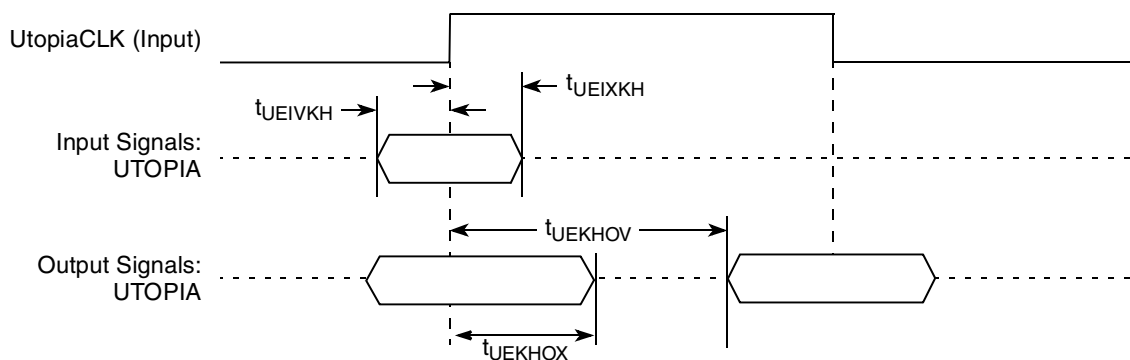

Figure 46. UTOPIA AC Timing (External Clock) Diagram

Figure 47 shows the UTOPIA timing with internal clock.

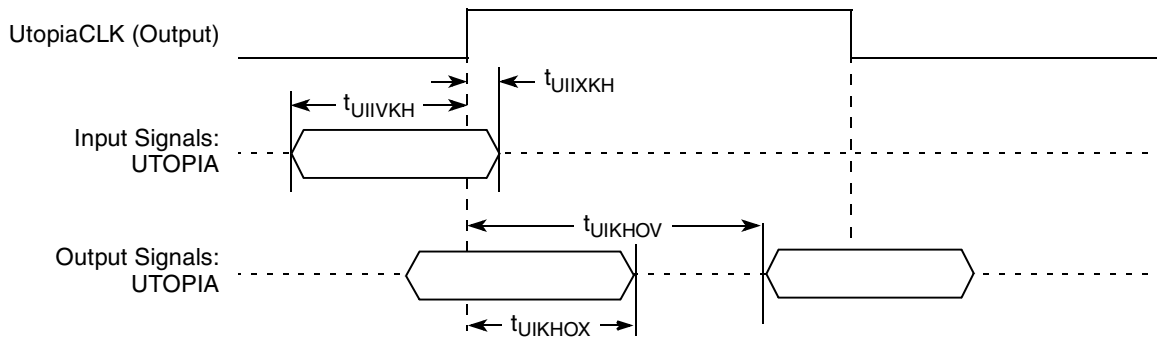


Figure 47. UTOPIA AC Timing (Internal Clock) Diagram

19 HDLC, BISYNC, Transparent, and Synchronous UART

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), BISYNC, transparent, and synchronous UART protocols of the MPC8358E.

19.1 HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Table 60 provides the DC electrical characteristics for the device HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 60. HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 10	μA

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8358E.

20.1 USB DC Electrical Characteristics

Table 63 provides the DC electrical characteristics for the USB interface.

Table 63. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.4$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V
Input current	I_{IN}	—	± 10	μA

20.2 USB AC Electrical Specifications

Table 64 describes the general timing parameters of the USB interface of the device.

Table 64. USB General Timing Parameters

Parameter	Symbol ¹	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(state)(signal)}$ for receive signals and $t_{(first\ two\ letters\ of\ functional\ block)(state)(signal)}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
- Skew measurements are done at $OV_{DD}/2$ of the rising or falling edge of the signals.

Figure 51 provide the AC test load for the USB.

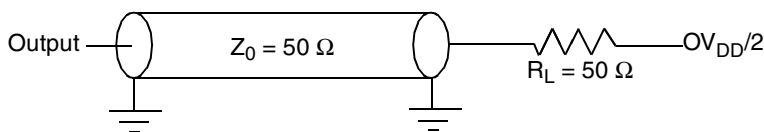


Figure 51. USB AC Test Load

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV _{DD}	C19, C22, C25, G24, J18, J19, J20, J24, K19, K20, K26, L20, M20, M26, N19, N20, P20, P27, R20, T19, T20, T27, U19, U20, U25, V19, V20, W20, W26, Y20, AA24, AB28, AC21, AC28, AD28, AF21, AF25	Power for DDR DRAM I/O Voltage (2.5 V or 1.8 V)	GV _{DD}	—
LV _{DD0}	F3, J9	—	LV _{DD0}	—
LV _{DD1}	P3, P10	—	LV _{DD1}	10
LV _{DD2}	R4, R10	—	LV _{DD2}	10
V _{DD}	M12, M13, M16, M17, N10, N12, N13, N14, N15, N16, N17, P12, P13, P14, P15, P16, P17, R12, R13, R16, R17, T12, T13, T16, T17, U12, U13, U14, U15, U16, U17, V12, V13, V16, V17, W11, W12, W13, W15, W16, W17, Y16, Y17	Power for Core (1.2 V)	V _{DD}	—
OV _{DD}	C6, C12, D17, J11, J13, J14, K3, K9, K10, K12, K15, K16, L10, M9, N9, T9, U9, V3, V10, W9, W10, W14, Y9, Y10, Y12, Y13, Y15, AA3, AE6, AE16, AF11, AF20	PCI, 10/100 Ethernet, and other Standard (3.3 V)	OV _{DD}	—
MVREF1	J27	I	DDR Referenc e Voltage	—
MVREF2	Y24	I	DDR Referenc e Voltage	—
No Connect				
NC	F23, G23, H23, J23, K23, L23, M23, N23, P23, R23, T23, U23, V23, W23, Y23, AA23, AB23, AC23	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to OV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to OV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. This pin must always be tied to GV_{DD}.
10. Refers to *MPC8360E PowerQUICC II™ Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins” for information about the two UCC2 Ethernet interface options.
11. It is recommended that MDIC0 be tied to GND using an 18.2 Ω resistor and MDIC1 be tied to DDR power using an 18.2 Ω resistor for DDR2.

The system VCO frequency is derived from the following equations:

- $csb_clk = \{PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV)\} \times SPMF$
- System VCO Frequency = $csb_clk \times VCO \text{ divider}$ (if both RCWL[DDRCM] and RCWL[LBCM] are cleared)
OR
- System VCO frequency = $2 \times csb_clk \times VCO \text{ divider}$ (if either RCWL[DDRCM] or RCWL[LBCM] are set).

As described in [Section 22, “Clocking,”](#) the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (csb_clk). [Table 70](#) shows the expected frequency values for the CSB frequency for select csb_clk to CLKIN/PCI_SYNC_IN ratios.

Table 70. CSB Frequency Options

CFG_CLKIN_DIV at Reset ¹	SPMF	csb_clk: Input Clock Ratio ²	Input Clock Frequency (MHz) ²					
			16.67	25	33.33	66.67		
			csb_clk Frequency (MHz)					
Low	0010	2:1				133		
Low	0011	3:1				100	200	
Low	0100	4:1				100	133	266
Low	0101	5:1				125	166	333
Low	0110	6:1	100	150	200			
Low	0111	7:1	116	175	233			
Low	1000	8:1	133	200	266			
Low	1001	9:1	150	225	300			
Low	1010	10:1	166	250	333			
Low	1011	11:1	183	275				
Low	1100	12:1	200	300				
Low	1101	13:1	216	325				
Low	1110	14:1	233					
Low	1111	15:1	250					
Low	0000	16:1	266					
High	0010	2:1				133		
High	0011	3:1				100	200	
High	0100	4:1				133	266	
High	0101	5:1				166	333	

23.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J , can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

23.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package will be approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device. At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JA}$ = junction to board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.